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TG 2800 MAIL ROOM

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(71) Patentee: Samsung Electronics Co., Ltd.

(54) Title of the Invention:

Method of Fabricating Capacitor for Use in Semiconductor Device

(57) Abstract:

Provided is a method of fabricating a capacitor. This method includes forming a lower electrode using a TiN or WN layer on a semiconductor substrate, preprocessing the lower electrode using p-NH₃, forming a dielectric layer on the preprocessed lower electrode, and forming an upper electrode on the dielectric layer. With this method, a dielectric layer can be evenly and regularly formed on a lower electrode so as to prevent a local increase in a leakage current due to a current generated by an upper electrode.